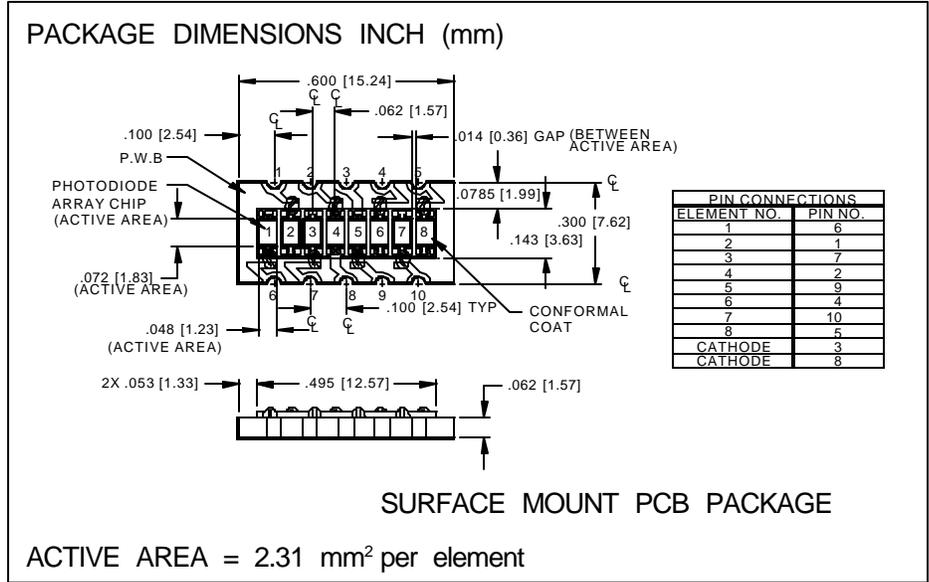
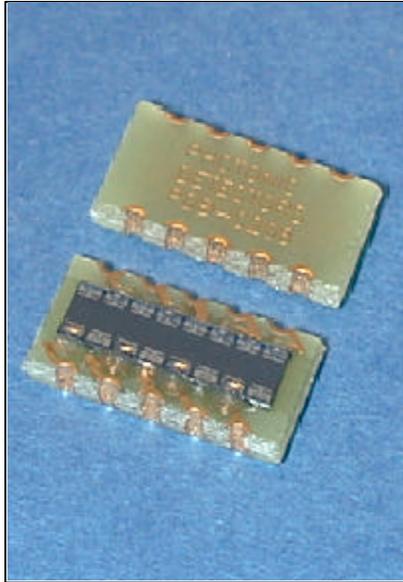


# PHOTONIC DETECTORS INC.

## Silicon Photodiode Array, Photoconductive 8 element Type PDB-C208



### FEATURES

- .062 inch centers
- Low cost
- Blue enhanced
- Low dark current

### DESCRIPTION

The **PDB-C208** is a silicon, PIN planar diffused, blue enhanced linear array photodiode. Ideal for high speed photoconductive applications. Packaged in low profile surface mount PCB substrate.

### APPLICATIONS

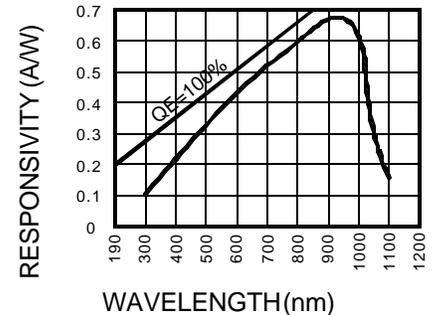
- Cardreader
- Scanners
- Instrumentation
- Characterrecognition

### ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V <sub>BR</sub>	Reverse Voltage		50	V
T <sub>STG</sub>	Storage Temperature	-40	+100	°C
T <sub>O</sub>	Operating Temperature Range	-20	+75	°C
T <sub>S</sub>	Soldering Temperature*		+265	°C
I <sub>L</sub>	Light Current		0.5	mA

\*edge of PCB for 3secs max

### SPECTRAL RESPONSE



### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>SC</sub>	Short Circuit Current	H = 100 fc, 2850 K	18	28		μA
I <sub>D</sub>	Dark Current	H = 0, V <sub>R</sub> = 5 V		5	50	nA
R <sub>SH</sub>	Shunt Resistance	H = 0, V <sub>R</sub> = 10 mV	100	200		MΩ
TC R <sub>SH</sub>	R <sub>SH</sub> Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8		% / °C
C <sub>J</sub>	Junction Capacitance	H = 0, V <sub>R</sub> = 0 V**		40	60	pF
λ <sub>range</sub>	Spectral Application Range	Spot Scan	350		1100	nm
λ <sub>p</sub>	Spectral Response - Peak	Spot Scan		950		nm
V <sub>BR</sub>	Breakdown Voltage	I = 10 μA	15	30		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 10 V @ Peak		3x10 <sup>-14</sup>		W/√Hz
tr	Response Time	RL = 50 Ω V <sub>R</sub> = 10 V		15		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. \*\*f=1 MHz

[FORMNO.100-PDB-C208 REVE]